

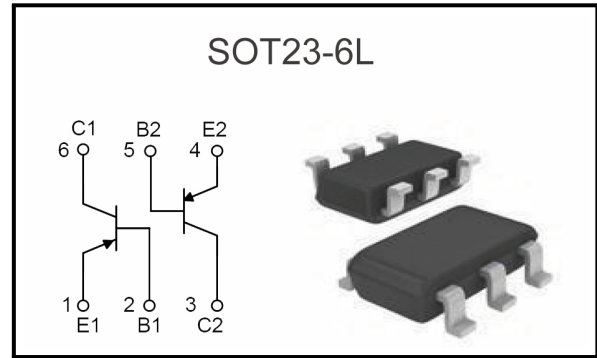
MMBT5401D

Dual PNP Plastic-Encapsulate Transistor

Features

- $V_{CE} = -150V$
- $I_C = -0.2A$
- $f_T = 100MHz @ V_{CE} = -10V, I_C = -10mA, f = 100MHz$

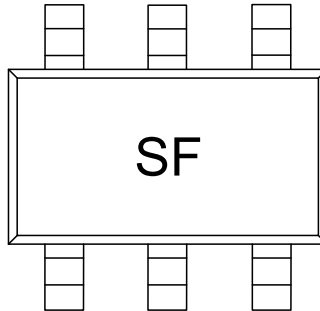
Package



Description

- Epitaxial planar die constructio
- SOT23-6L Plastic Package.

Marking



Ordering information

Order code	Package	Marking	Base qty	Delivery mode
MMBT5401D	SOT23-6L	SF	3K	Tape and reel

Absolute Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.2	A
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	400	$^\circ C/W$
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55 to + 150	$^\circ C$



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Electrical Characteristics (T_A=+25°C, unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-100μA, I _E =0	-160	-	-	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA, I _B =0	-150	-	-	
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10μA, I _C =0	-5	-	-	
I _{CBO}	Collector cut-off current	V _{CB} =-120V, I _E =0	-	-	-50	nA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V, I _C =0	-	-	-50	
h _{FE(1)}	DC current gain	V _{CE} =-5V, I _C =-1mA	50	-	-	
h _{FE(2)}		V _{CE} =-5V, I _C =-10mA	100	-	300	
h _{FE(3)}		V _{CE} =-5V, I _C =-50mA	50	-	-	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-10mA, I _B =-1mA	-	-	-0.2	V
		I _C =-50mA, I _B =-5mA	-	-	-0.5	
V _{BE(sat)}	Base-emitter saturation voltage	I _C =-10mA, I _B =-1mA	-	-	-1.00	
		I _C =-50mA, I _B =-5mA	-	-	-1.00	
f _T	Transition frequency	V _{CE} =-10V, I _C =10mA, f=100MHZ	100	-	-	MHZ
C _{ob}	Collector output capacitance	V _{CB} =-10V, I _E =0, f=1MHZ			6	pF

Note: Pulse test: pulse width ≤ 300us, duty cycle ≤ 2.0%



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Typical Performance Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1 : Static Characteristic

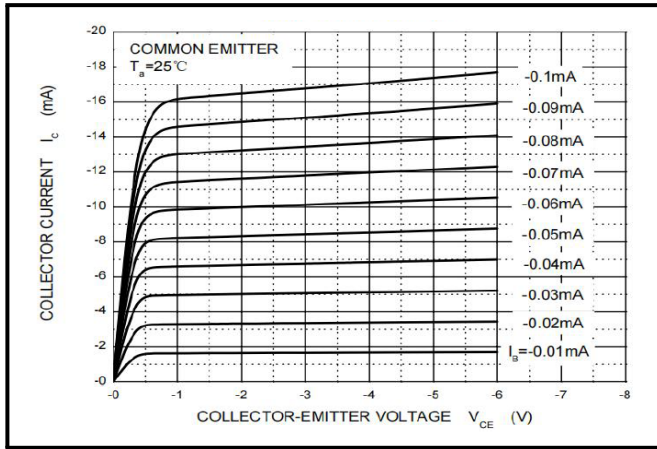


Figure 2 : $h_{FE} - I_C$

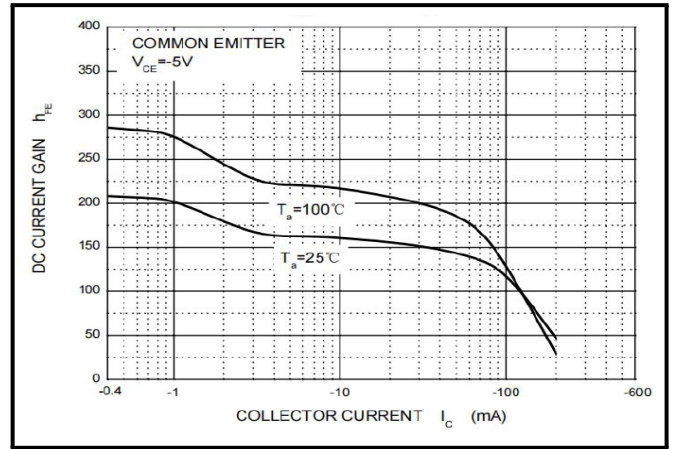


Figure 3 : $V_{BE(sat)} - I_C$

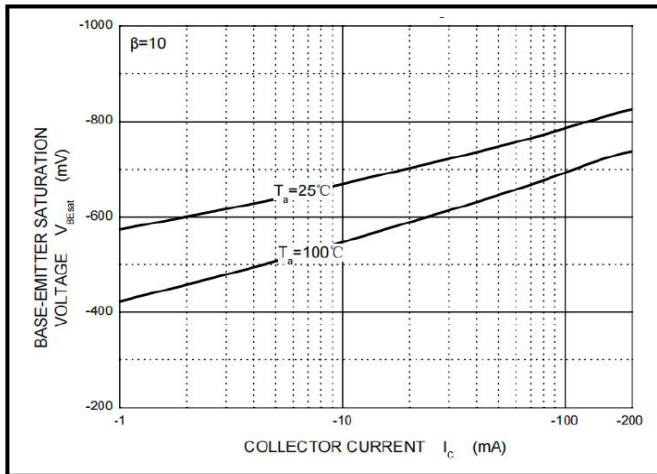


Figure 4 : $V_{CE(sat)} - I_C$

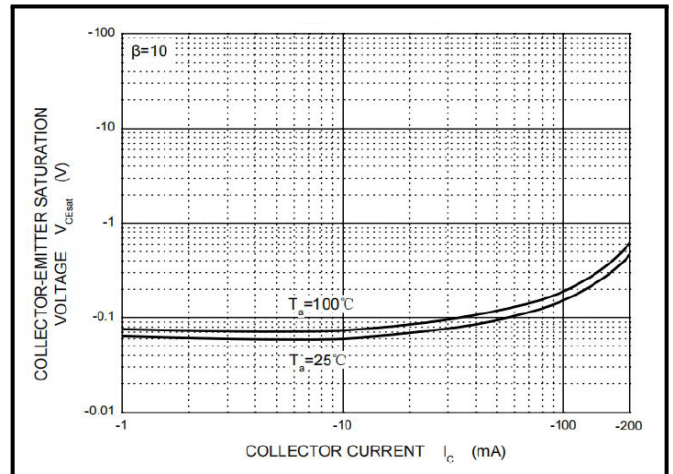


Figure 5 : $I_C - V_{BE}$

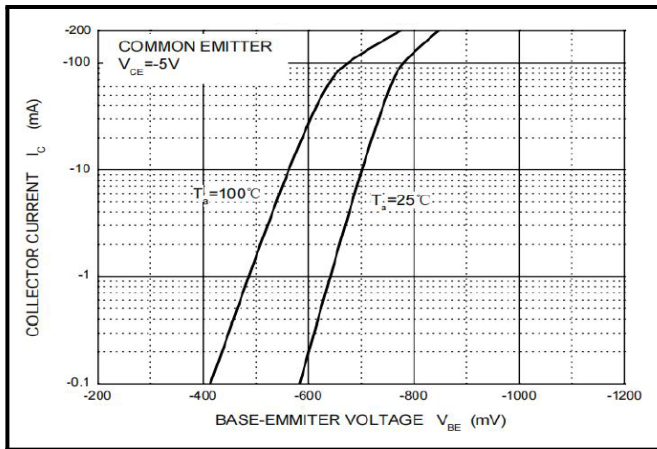
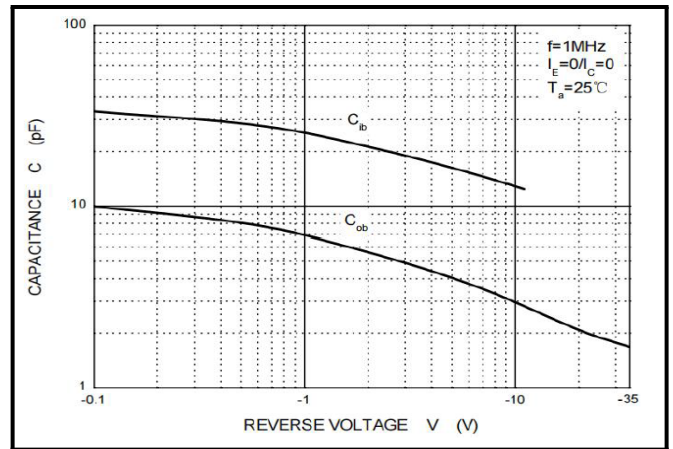


Figure 6 : $C_{ob}/C_{ib} - V_{CB}/V_{EB}$



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Figure 7 : f_T — I_C

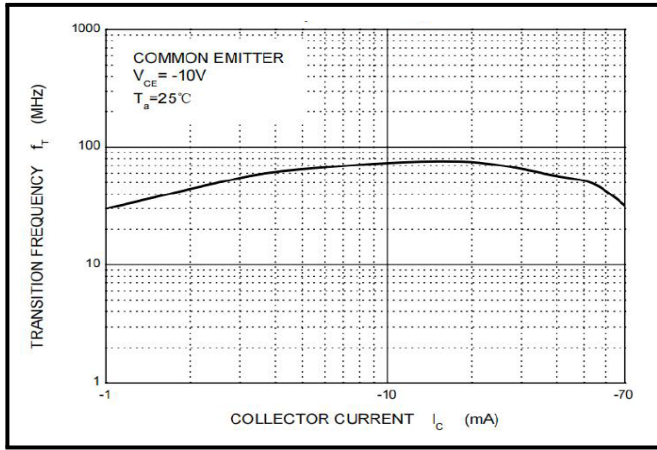
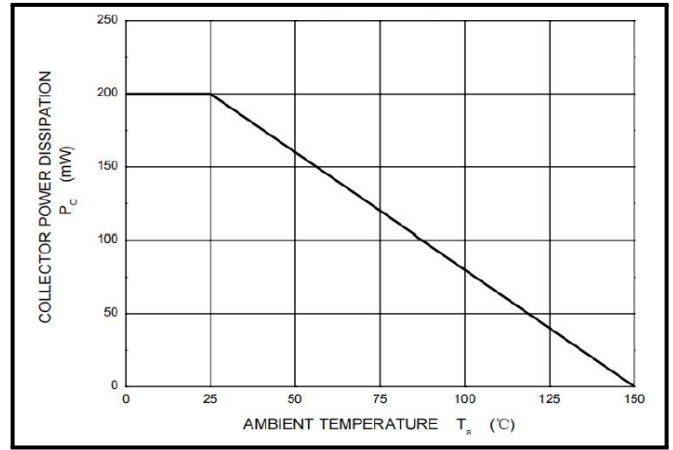


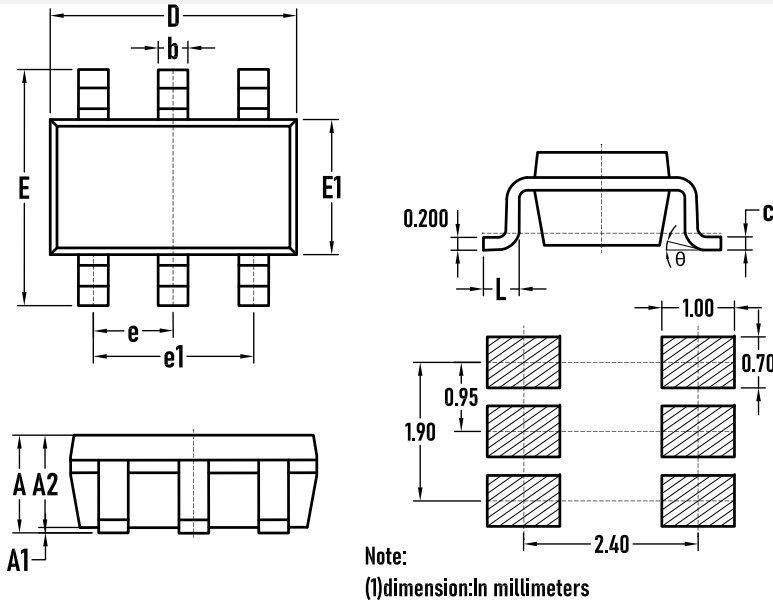
Figure 8 : P_C — T_a



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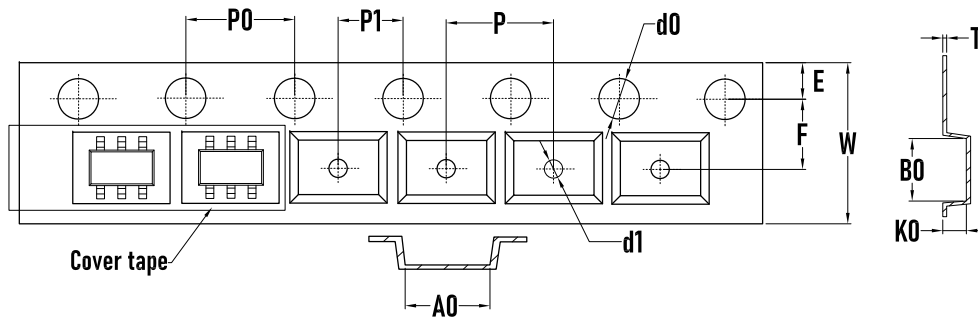
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Outline Drawing - SOT23-6L



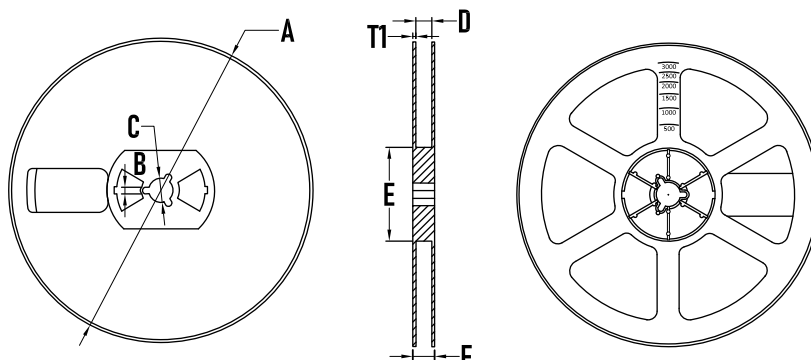
SYMBOL	MILLIMETER		Inches	
	MIN	MAX	MIN	MAX
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Packaging Tape - SOT23-6L



SYMBOL	MILLIMETER
A0	3.25±0.1
B0	3.3±0.1
d0	1.55±0.1
d1	1.0±0.1
E	1.75±0.1
F	3.50±0.1
K0	1.38±0.1
P	4.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	8.00±0.2
T	0.2±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	177.8±0.2
B	2.7±0.2
C	13.5±0.2
D	9.6±0.3
E	54.5±0.2
F	12.3±0.3
T1	1.0±0.2
Quantity	3000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

Revision: 2022-Jan-1-A

